



STW15NK90Z

N-channel 900V - 0.40Ω - 15A - TO-247
Zener - Protected SuperMESH™ PowerMOSFET

General features

| Type | V _{DSS} (@T _{Jmax}) | R _{DS(on)} | I _D | P _W |
|------------|---|---------------------|----------------|----------------|
| STW15NK90Z | 900 V | < 0.55 Ω | 15 A | 350W |

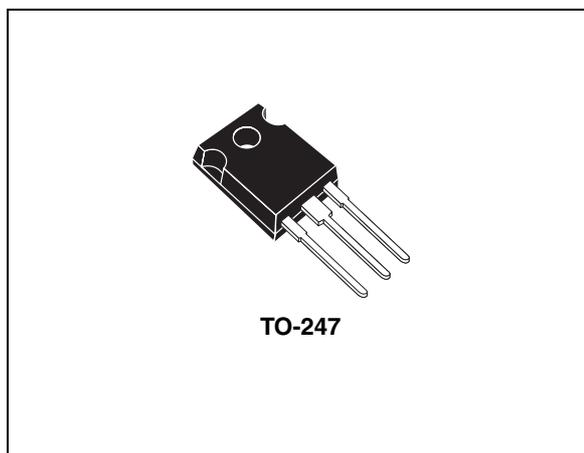
- Extremely high dv/dt capability
- 100% avalanche tested
- Gate charge minimized
- Very low intrinsic capacitances
- Very good manufacturing repeatability

Description

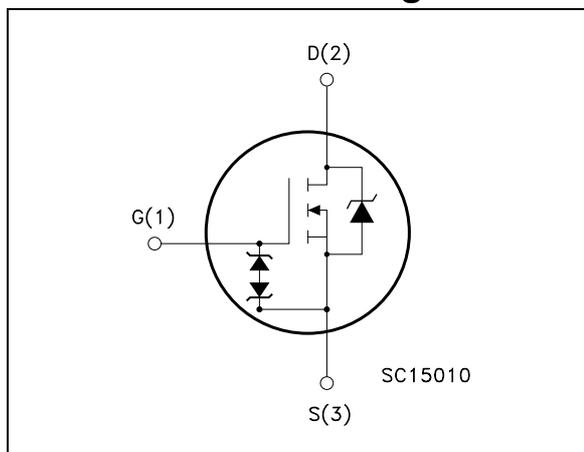
The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

Applications

- Switching application



Internal schematic diagram



Order codes

| Part number | Marking | Package | Packaging |
|-------------|----------|---------|-----------|
| STW15NK90Z | W15NK90Z | TO-247 | Tube |

Contents

| | | |
|----------|--|-----------|
| 1 | Electrical ratings | 3 |
| 1.1 | Protection features of gate-to-source zener diodes | 4 |
| 2 | Electrical characteristics | 5 |
| 2.1 | Electrical characteristics (curves) | 7 |
| 3 | Test circuit Package mechanical data | 10 |
| 4 | Package mechanical data | 11 |
| 5 | Revision history | 13 |

1 Electrical ratings

Table 1. Absolute maximum ratings

| Symbol | Parameter | Value | Unit |
|--------------------|---|------------|---------------|
| V_{DS} | Drain-source voltage ($V_{GS} = 0$) | 900 | V |
| V_{DGR} | Drain-gate voltage ($R_{GS} = 20K\Omega$) | 900 | V |
| V_{GS} | Gate-source voltage | ± 30 | V |
| I_D | Drain current (continuous) at $T_C = 25^\circ C$ | 15 | A |
| I_D | Drain current (continuous) at $T_C = 100^\circ C$ | 9.5 | A |
| $I_{DM}^{(1)}$ | Drain current (pulsed) | 60 | A |
| P_{TOT} | Total dissipation at $T_C = 25^\circ C$ | 350 | W |
| | Derating Factor | 2.77 | W/ $^\circ C$ |
| $V_{ESD (G-S)}$ | Gate source ESD(HBM-C=100pF, R=1,5K Ω) | 6000 | V |
| $dv/dt^{(2)}$ | Peak diode recovery voltage slope | 4.5 | V/ns |
| T_J T_{stg} | Operating junction temperature Storage temperature | -55 to 150 | $^\circ C$ |

1. Pulse width limited by safe operating area

2. $I_{SD} \leq 15 A$, $di/dt \leq 200 A/\mu s$, $V_{DD} \leq 900 V$, $T_J \leq T_{JMAX}$

Table 2. Thermal data

| Symbol | Parameter | Value | Unit |
|----------------|--|-------|--------------|
| $R_{thj-case}$ | Thermal resistance junction-case Max | 0.36 | $^\circ C/W$ |
| R_{thj-a} | Thermal resistance junction-ambient Max | 50 | $^\circ C/W$ |
| T_l | Maximum lead temperature for soldering purpose | 300 | $^\circ C$ |

Table 3. Avalanche characteristics

| Symbol | Parameter | Value | Unit |
|----------|--|-------|------|
| I_{AR} | Avalanche current, repetitive or not-repetitive (pulse width limited by T_J Max) | 15 | A |
| E_{AS} | Single pulse avalanche energy (starting $T_J = 25^\circ C$, $I_d = I_{AR}$, $V_{dd} = 50V$) | 360 | mJ |

Table 4. Gate-source zener diode

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|------------|-------------------------------|--------------------------------------|------|------|------|------|
| BV_{GSO} | Gate-source breakdown voltage | $I_{gs}=\pm 1\text{mA}$ (Open Drain) | 30 | | | V |

1.1 Protection features of gate-to-source zener diodes

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

2 Electrical characteristics

($T_{CASE}=25^{\circ}C$ unless otherwise specified)

Table 5. On/off states

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------|--|--|------|------|----------|--------------------|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage | $I_D = 1mA, V_{GS} = 0$ | 900 | | | V |
| I_{DSS} | Zero gate voltage drain current ($V_{GS} = 0$) | $V_{DS} = \text{Max rating},$ $V_{DS} = \text{Max rating},$ $T_c = 125^{\circ}C$ | | | 1 50 | μA μA |
| I_{GSS} | Gate body leakage current ($V_{GS} = 0$) | $V_{GS} = \pm 20V$ | | | ± 10 | μA |
| $V_{GS(th)}$ | Gate threshold voltage | $V_{DS} = V_{GS}, I_D = 150 \mu A$ | 3 | 3.75 | 4.5 | V |
| $R_{DS(on)}$ | Static drain-source on resistance | $V_{GS} = 10V, I_D = 7.5 A$ | | 0.40 | 0.55 | Ω |

Table 6. Dynamic

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-------------------|-------------------------------|--|------|------|------|------|
| $g_{fs}^{(1)}$ | Forward transconductance | $V_{DS} = 15V, I_D = 7.5 A$ | | 15 | | S |
| C_{iss} | Input capacitance | $V_{DS} = 25V, f = 1 \text{ MHz}, V_{GS} = 0$ | | 6100 | | pF |
| C_{oss} | Output capacitance | | | 465 | | pF |
| C_{rss} | Reverse transfer capacitance | | | 96 | | pF |
| $C_{osseq}^{(2)}$ | Equivalent output capacitance | $V_{GS} = 0, V_{DS} = 0V \text{ to } 720V$ | | 230 | | pF |
| $t_{d(on)}$ | Turn-on delay time | $V_{DD} = 450 V, I_D = 7.5A,$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see Figure 16) | | 42 | | ns |
| t_r | Rise time | | | 27 | | ns |
| $t_{d(off)}$ | Off-voltage rise time | | | 135 | | ns |
| t_f | Fall time | | | 35 | | ns |
| Q_g | Total gate charge | $V_{DD} = 720V, I_D = 15A$ $V_{GS} = 10V$ | | 190 | 256 | nC |
| Q_{gs} | Gate-source charge | | | 56 | | nC |
| Q_{gd} | Gate-drain charge | | | 70 | | nC |

1. Pulsed: pulse duration=300 μs , duty cycle 1.5%

2. $C_{oss eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Source drain diode

| Symbol | Parameter | Test conditions | Min | Typ. | Max | Unit |
|-----------------------------------|--|---|-----|-------------------|-----|--------------------|
| I_{SD} | Source-drain current | | | | 15 | A |
| $I_{SDM}^{(1)}$ | Source-drain current (pulsed) | | | | 60 | A |
| $V_{SD}^{(2)}$ | Forward on voltage | $I_{SD}=15A, V_{GS}=0$ | | | 1.6 | V |
| t_{rr} Q_{rr} I_{RRM} | Reverse recovery time Reverse recovery charge Reverse recovery current | $I_{SD}=15 A,$ $di/dt = 100A/\mu s,$ $V_{DD}=100 V, T_j=25^\circ C$ (see Figure 18) | | 748 10.5 28 | | ns μC A |
| t_{rr} Q_{rr} I_{RRM} | Reverse recovery time Reverse recovery charge Reverse recovery current | $I_{SD}=15 A,$ $di/dt = 100A/\mu s,$ $V_{DD}=100V, T_j=150^\circ C$ (see Figure 18) | | 900 13 28.5 | | ns μC A |

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

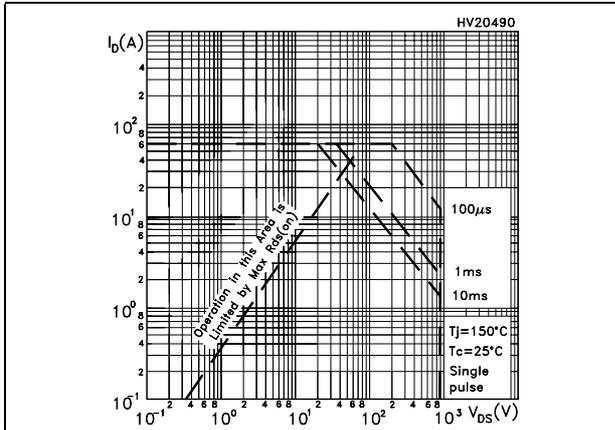


Figure 2. Thermal impedance

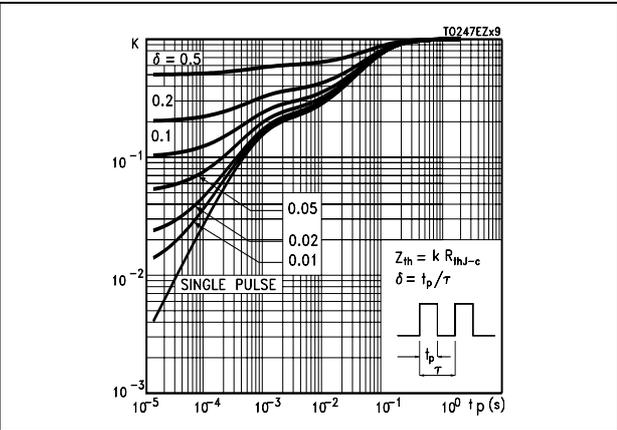


Figure 3. Output characteristics

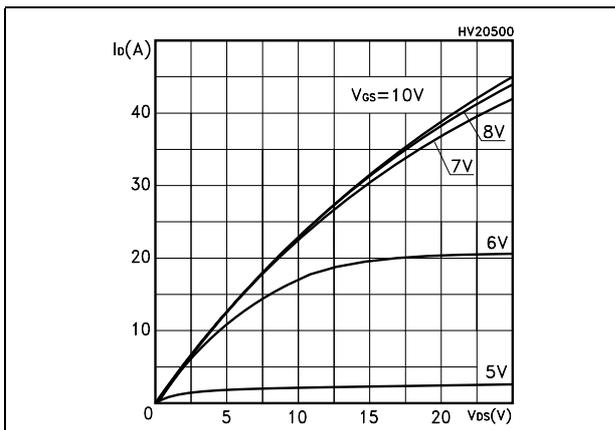


Figure 4. Transfer characteristics

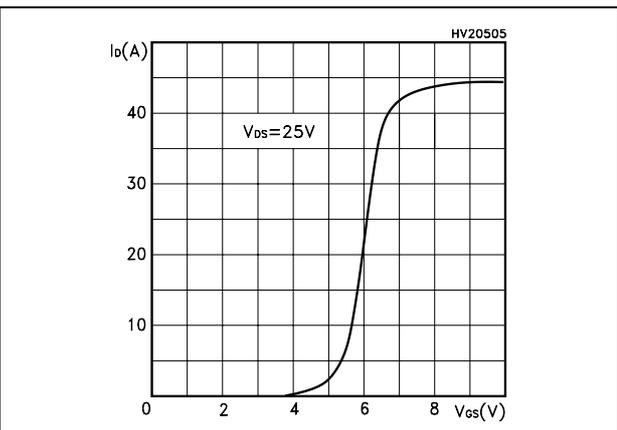


Figure 5. Transconductance

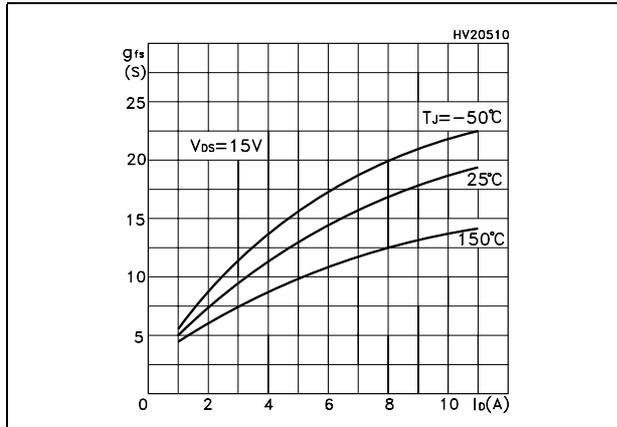


Figure 6. Static drain-source on resistance

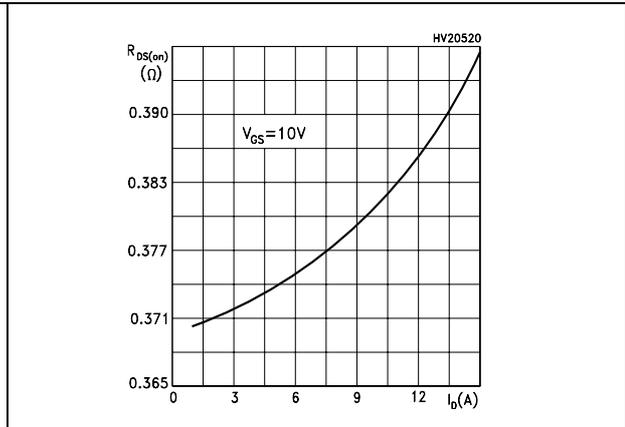


Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations

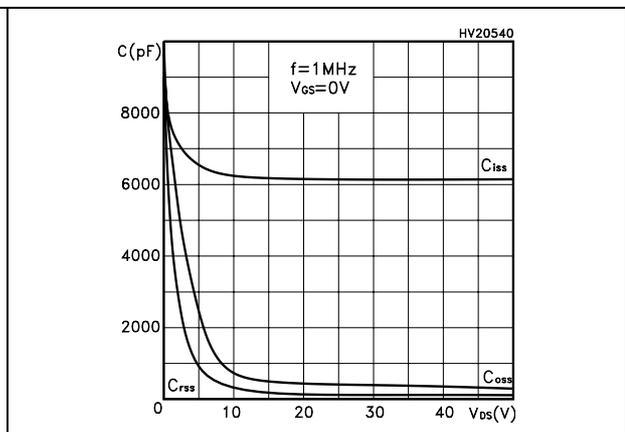
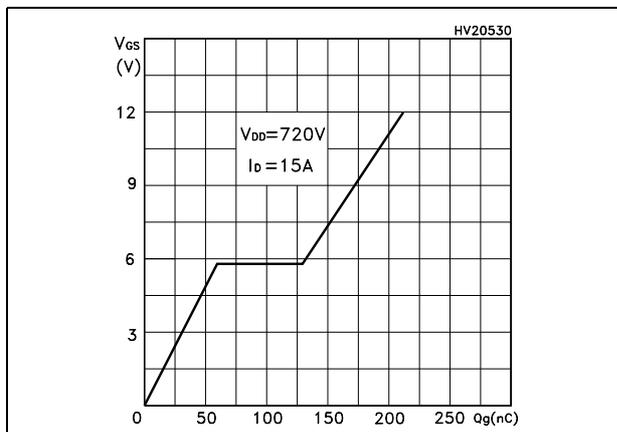


Figure 9. Normalized gate threshold voltage vs temperature

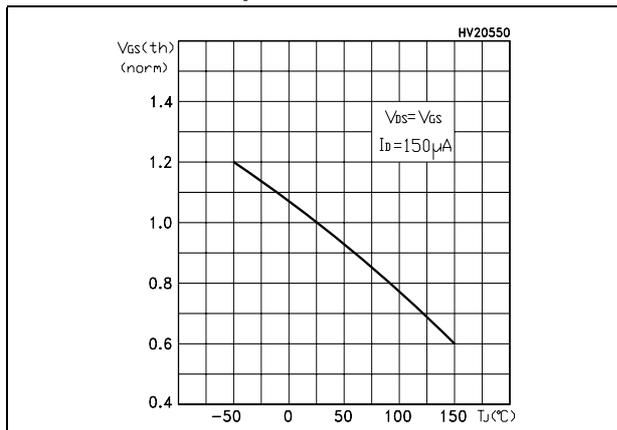


Figure 10. Normalized on resistance vs temperature

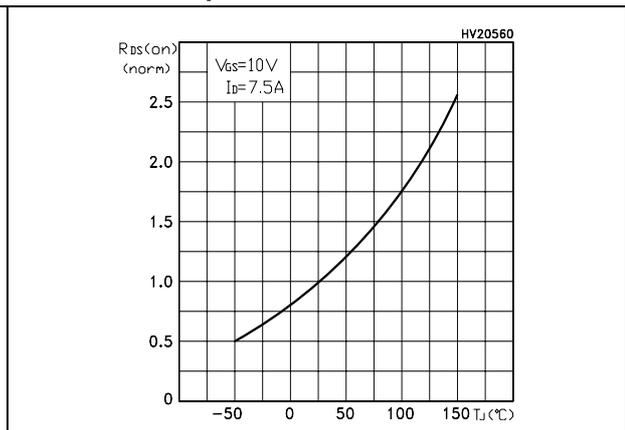


Figure 11. Source-drain diode forward characteristics

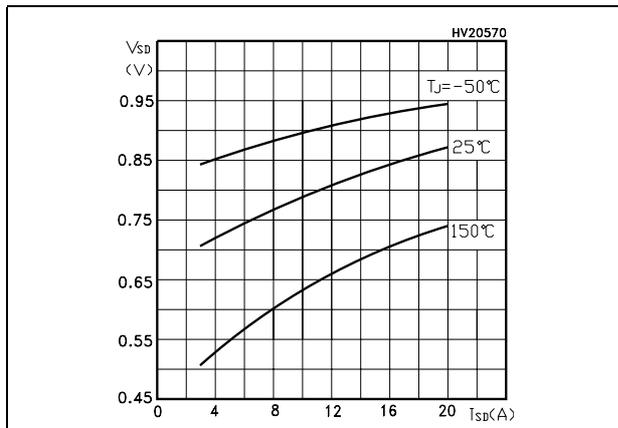


Figure 12. Normalized B_{VDSS} vs temperature

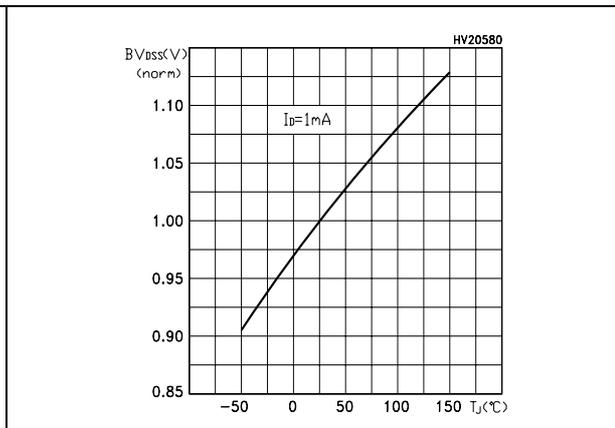
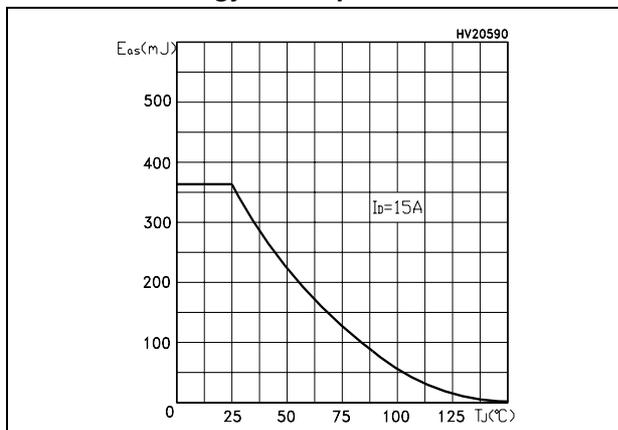


Figure 13. Maximum avalanche energy vs temperature



3 Test circuit Package mechanical data

Figure 14. Unclamped Inductive load test circuit

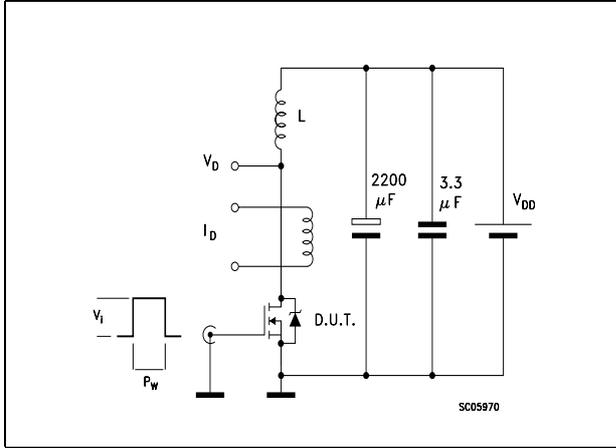


Figure 15. Unclamped Inductive waveform

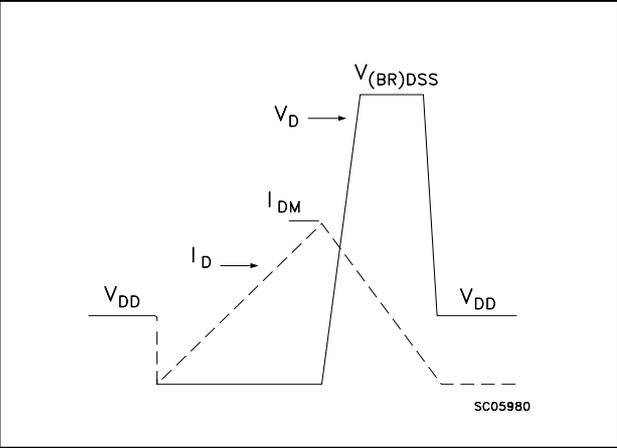


Figure 16. Switching times test circuit for resistive load

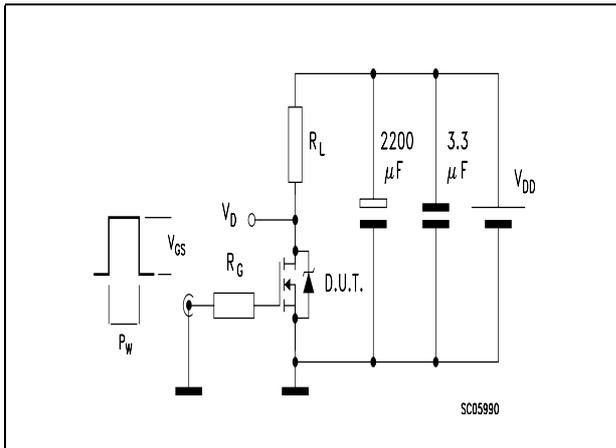


Figure 17. Gate charge test circuit

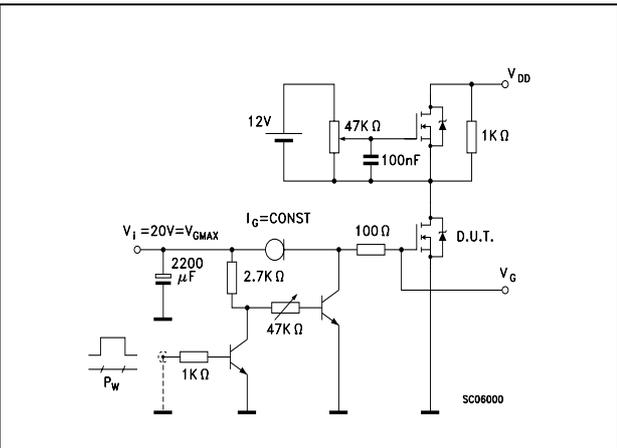
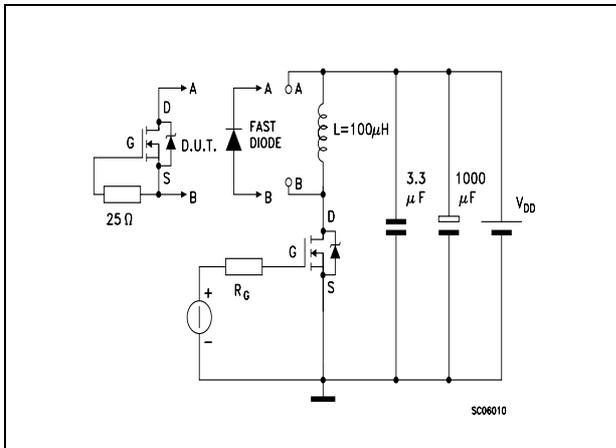


Figure 18. Test circuit for inductive load switching and diode recovery times

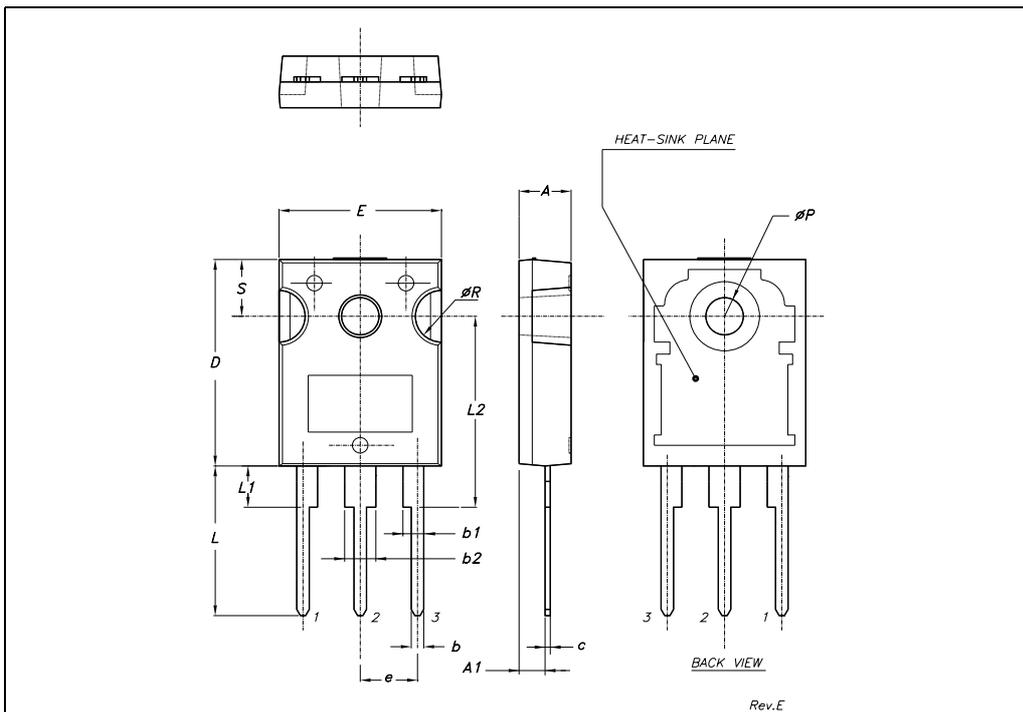


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TO-247 MECHANICAL DATA

| DIM. | mm. | | | inch | | |
|------|-------|-------|-------|-------|-------|-------|
| | MIN. | TYP | MAX. | MIN. | TYP. | MAX. |
| A | 4.85 | | 5.15 | 0.19 | | 0.20 |
| A1 | 2.20 | | 2.60 | 0.086 | | 0.102 |
| b | 1.0 | | 1.40 | 0.039 | | 0.055 |
| b1 | 2.0 | | 2.40 | 0.079 | | 0.094 |
| b2 | 3.0 | | 3.40 | 0.118 | | 0.134 |
| c | 0.40 | | 0.80 | 0.015 | | 0.03 |
| D | 19.85 | | 20.15 | 0.781 | | 0.793 |
| E | 15.45 | | 15.75 | 0.608 | | 0.620 |
| e | | 5.45 | | | 0.214 | |
| L | 14.20 | | 14.80 | 0.560 | | 0.582 |
| L1 | 3.70 | | 4.30 | 0.14 | | 0.17 |
| L2 | | 18.50 | | | 0.728 | |
| øP | 3.55 | | 3.65 | 0.140 | | 0.143 |
| øR | 4.50 | | 5.50 | 0.177 | | 0.216 |
| S | | 5.50 | | | 0.216 | |



5 Revision history

Table 8. Revision history

| Date | Revision | Changes |
|-------------|-----------------|---------------------------------|
| 09-Sep-2004 | 1 | Preliminary |
| 08-Sep-2005 | 2 | Complete datasheet |
| 31-Jul-2005 | 3 | New template, no content change |

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2006 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

Компания «Океан Электроники» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Поставка оригинальных импортных электронных компонентов напрямую с производств Америки, Европы и Азии, а так же с крупнейших складов мира;
- Широкая линейка поставок активных и пассивных импортных электронных компонентов (более 30 млн. наименований);
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Помощь Конструкторского Отдела и консультации квалифицированных инженеров;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
- Поставка специализированных компонентов военного и аэрокосмического уровня качества (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Actel, Aeroflex, Peregrine, VPT, Syfer, Eurofarad, Texas Instruments, MS Kennedy, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Компания «Океан Электроники» является официальным дистрибьютором и эксклюзивным представителем в России одного из крупнейших производителей разъемов военного и аэрокосмического назначения «JONHON», а так же официальным дистрибьютором и эксклюзивным представителем в России производителя высокотехнологичных и надежных решений для передачи СВЧ сигналов «FORSTAR».



JONHON

«JONHON» (основан в 1970 г.)

Разъемы специального, военного и аэрокосмического назначения:

(Применяются в военной, авиационной, аэрокосмической, морской, железнодорожной, горно- и нефтедобывающей отраслях промышленности)

«FORSTAR» (основан в 1998 г.)

ВЧ соединители, коаксиальные кабели, кабельные сборки и микроволновые компоненты:

(Применяются в телекоммуникациях гражданского и специального назначения, в средствах связи, РЛС, а так же военной, авиационной и аэрокосмической отраслях промышленности).



Телефон: 8 (812) 309-75-97 (многоканальный)

Факс: 8 (812) 320-03-32

Электронная почта: ocean@oceanchips.ru

Web: <http://oceanchips.ru/>

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, д. 2, корп. 4, лит. А